SPP7401

DESCRIPTION

The SPP7401 is the P-Channel logic enhancement mode power field effect transistors are produced using high cell density , DMOS trench technology.

This high density process is especially tailored to minimize on-state resistance.

These devices are particularly suited for low voltage application such as cellular phone and notebook computer power management and other battery powered circuits where high-side switching , and low in-line power loss are needed in a very small outline surface mount package.

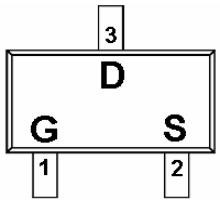
APPLICATIONS

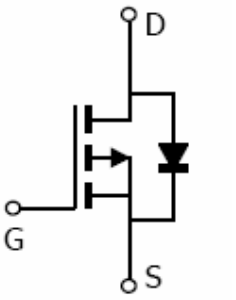
- Power Management in Note book
- Portable Equipment
- Battery Powered System
- DC/DC Converter
- Load Switch
- DSC
- LCD Display inverter

FEATURES

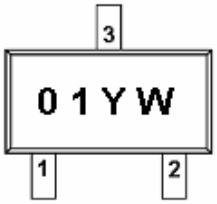
- -30V/-2.8A,$R_{DS(ON)}$=115mΩ@V_{GS}=- 10V
- -30V/-2.5A,$R_{DS(ON)}$=125mΩ@V_{GS}=-4.5V
- -30V/-1.5A,$R_{DS(ON)}$=170mΩ@V_{GS}=-2.5V
- -30V/-1.0A,$R_{DS(ON)}$=240mΩ@V_{GS}=-1.8V
- Super high density cell design for extremely low RDS (ON)
- Exceptional on-resistance and maximum DC current capability
- SOT-323 (SC–70) package design

PIN CONFIGURATION (SOT-323 ; SC-70)





PART MARKING



Y : Year Code
W : Week Code

SPP7401

PIN DESCRIPTION

Pin	Symbol	Description
1	G	Gate
2	S	Source
3	D	Drain

ORDERING INFORMATION

Part Number	Package	Part Marking
SPP7401S32RG	SOT-323	01YW

※ Week Code : A ~ Z(1 ~ 26) ; a ~ z(27 ~ 52)
※ SPP7401S32RG : Tape Reel ; Pb – Free

ABSOULTE MAXIMUM RATINGS

(T_A=25℃ Unless otherwise noted)

Parameter		Symbol	Typical	Unit
Drain-Source Voltage		V_{DSS}	-30	V
Gate –Source Voltage		V_{GSS}	±12	V
Continuous Drain Current(T_J=150℃)	T_A=25℃	I_D	-2.8	A
	T_A=70℃		-2.1	
Pulsed Drain Current		I_{DM}	-8	A
Continuous Source Current(Diode Conduction)		I_S	-1.4	A
Power Dissipation	T_A=25℃	P_D	0.33	W
	T_A=70℃		0.21	
Operating Junction Temperature		T_J	-55/150	℃
Storage Temperature Range		T_{STG}	-55/150	℃
Thermal Resistance-Junction to Ambient		$R_{\theta JA}$	105	℃/W

SPP7401

ELECTRICAL CHARACTERISTICS

(T_A=25℃ Unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS}=0V,I_D=-250uA	-30			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=-250uA	-0.4		-1.0	
Gate Leakage Current	I_{GSS}	V_{DS}=0V,V_{GS}=±12V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=-24V,V_{GS}=0V			-1	uA
		V_{DS}=-24V,V_{GS}=0V T_J=85℃			-5	
On-State Drain Current	$I_{D(on)}$	V_{DS}= -5V,V_{GS} =-4.5V	-4			A
Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS}=-10V,I_D=-2.8A		0.105	0.115	Ω
		V_{GS}=-4.5V,I_D=-2.5A		0.125	0.135	
		V_{GS}=-2.5V,I_D=-1.5A		0.155	0.170	
		V_{GS}=-1.8V,I_D=-1.0A		0.210	0.240	
Forward Transconductance	gfs	V_{DS}=-10V,I_D=-2.8A		4		S
Diode Forward Voltage	V_{SD}	I_S=-1.2A,V_{GS} =0V		-0.8	-1.2	V
Dynamic						
Total Gate Charge	Q_g	V_{DS}=-15V ,V_{GS}=-4.5V I_D≡-2.0A		5.8		nC
Gate-Source Charge	Q_{gs}			0.8		
Gate-Drain Charge	Q_{gd}			1.5		
Input Capacitance	C_{iss}	V_{DS}=-15V ,V_{GS}=0V f=1MHz		380		pF
Output Capacitance	C_{oss}			55		
Reverse Transfer Capacitance	C_{rss}			40		
Turn-On Time	$t_{d(on)}$	V_{DD}=-15V ,R_L=15Ω I_D≡-1.0A ,V_{GEN}=-10V R_G=3Ω		6		ns
	t_r			3.9		
Turn-Off Time	$t_{d(off)}$			40		
	t_f			15		